



## Features

- High blocking voltage with low On-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Qrr)
- Halogen free, RoHS compliant

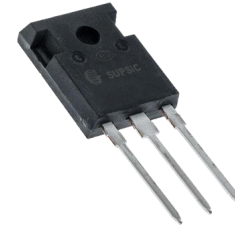
## Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency

## Applications

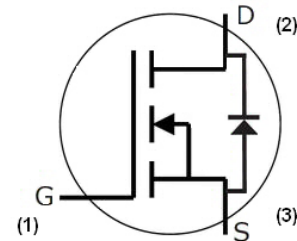
- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies

$V_{DS}$	1200 V
$I_D @ 25^\circ\text{C}$	32 A
$R_{DS(on)}$	75 m $\Omega$



TO-247-3

### Package



Ordering Part Number	Package	$T_J, T_{stg}$ Range
GC3M0075120D	TO 247-3	-55 - 150 °C
GC3M0075120D-A	TO 247-3	-40 - 175 °C

## Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{DSmax}$	Drain - Source Voltage	1200	V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GSmax}$	Gate - Source Voltage (dynamic)	-8/+19	V	AC ( $f > 1\text{ Hz}$ )	Note: 1
$V_{GSop}$	Gate - Source Voltage (static)	-4/+15	V	Static	Note: 2
$I_D$	Continuous Drain Current	32	A	$V_{GS} = 15\text{ V}, T_C = 25^\circ\text{C}$	Fig. 19
		23		$V_{GS} = 15\text{ V}, T_C = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	80	A	Pulse width $t_p$ limited by $T_{Jmax}$	Fig. 22
$P_D$	Power Dissipation	136	W	$T_C = 25^\circ\text{C}, T_J = 175^\circ\text{C}$	Fig. 20
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-40 to +175	°C		
$T_L$	Solder Temperature	260	°C	1.6mm (0.063") from case for 10s	
$M_d$	Mounting Torque	1	Nm	M3 or 6-32 screw	
		8.8			

Note (1): When using MOSFET Body Diode  $V_{GSmax} = -4\text{V}/+19\text{V}$

Note (2): MOSFET can also safely operate at 0/+15 V

**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.5	3.6	V	$V_{DS} = V_{GS}, I_D = 5\text{ mA}$	Fig. 11
			2.2		V	$V_{DS} = V_{GS}, I_D = 5\text{ mA}, T_J = 175^\circ\text{C}$	
$I_{DSS}$	Zero Gate Voltage Drain Current		1	100	$\mu\text{A}$	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	
$I_{GSS}$	Gate-Source Leakage Current		10	250	nA	$V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		75	90	m $\Omega$	$V_{GS} = 15\text{ V}, I_D = 20\text{ A}$	Fig. 4, 5, 6
			120			$V_{GS} = 15\text{ V}, I_D = 20\text{ A}, T_J = 175^\circ\text{C}$	
$g_{fs}$	Transconductance		12		S	$V_{DS} = 20\text{ V}, I_{DS} = 20\text{ A}$	Fig. 7
			13			$V_{DS} = 20\text{ V}, I_{DS} = 20\text{ A}, T_J = 175^\circ\text{C}$	
$C_{iss}$	Input Capacitance		1390		pF	$V_{GS} = 0\text{ V}, V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$ $V_{AC} = 25\text{ mV}$	Fig. 17, 18
$C_{oss}$	Output Capacitance		58				
$C_{riss}$	Reverse Transfer Capacitance		2				
$E_{oss}$	$C_{oss}$ Stored Energy		33		$\mu\text{J}$		Fig. 16
$E_{on}$	Turn-On Switching Energy (SiC Diode FWD)		564		$\mu\text{J}$	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}, I_D = 20\text{ A},$ $R_{G(ext)} = 0\ \Omega, L = 157\ \mu\text{H}, T_J = 150^\circ\text{C}$	Fig. 26, 29
$E_{off}$	Turn Off Switching Energy (SiC Diode FWD)		186				
$E_{on}$	Turn-On Switching Energy (Body Diode FWD)		924		$\mu\text{J}$	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}, I_D = 20\text{ A},$ $R_{G(ext)} = 0\ \Omega, L = 157\ \mu\text{H}, T_J = 150^\circ\text{C}$	Fig. 26, 29
$E_{off}$	Turn Off Switching Energy (Body Diode FWD)		162				
$t_{d(on)}$	Turn-On Delay Time		56		ns	$V_{DD} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$ $I_D = 20\text{ A}, R_{G(ext)} = 0\ \Omega,$ Timing relative to $V_{DS}$ Inductive load	Fig. 27, 28
$t_r$	Rise Time		17				
$t_{d(off)}$	Turn-Off Delay Time		32				
$t_f$	Fall Time		13				
$R_{G(int)}$	Internal Gate Resistance		9.0		$\Omega$	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$	
$Q_{gs}$	Gate to Source Charge		17		nC	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$ $I_D = 20\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
$Q_{gd}$	Gate to Drain Charge		20				
$Q_g$	Total Gate Charge		54				

**Reverse Diode Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_{SD}$	Diode Forward Voltage	4.5		V	$V_{GS} = -4\text{ V}, I_{SD} = 10\text{ A}$	Fig. 8, 9, 10
		4.0		V	$V_{GS} = -4\text{ V}, I_{SD} = 10\text{ A}, T_J = 175^\circ\text{C}$	
$I_S$	Continuous Diode Forward Current		26	A	$V_{GS} = -4\text{ V}, T_J = 25^\circ\text{C}$	Note 1
$I_{S,pulse}$	Diode pulse Current	80		A	$V_{GS} = -4\text{ V},$ pulse width $t_p$ limited by $T_{jmax}$	Note 1
$t_{rr}$	Reverse Recover time	48		ns	$V_{GS} = -4\text{ V}, I_{SD} = 20\text{ A}, V_R = 800\text{ V}$ $\text{dif}/\text{dt} = 2800\text{ A}/\mu\text{s}, T_J = 150^\circ\text{C}$	Note 1
$Q_{rr}$	Reverse Recovery Charge	279		nC		
$I_{rrm}$	Peak Reverse Recovery Current	9		A		

**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.97	1.1	$^\circ\text{C}/\text{W}$		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient		40			

Typical Performance

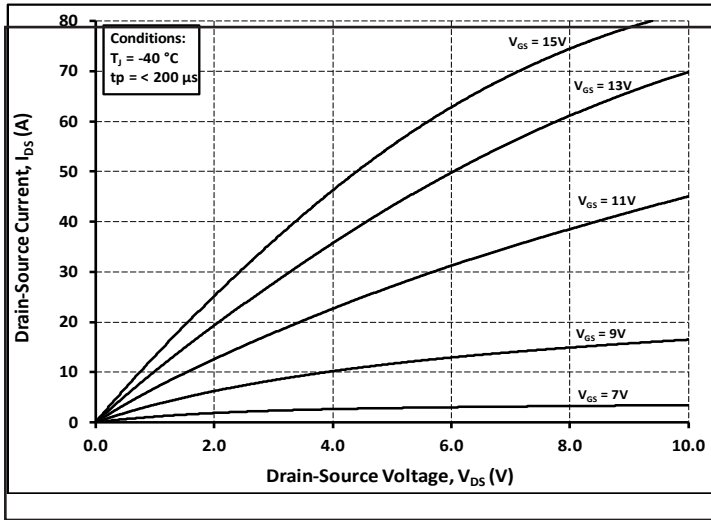


Figure 1. Output Characteristics  $T_J = -40\text{ }^\circ\text{C}$

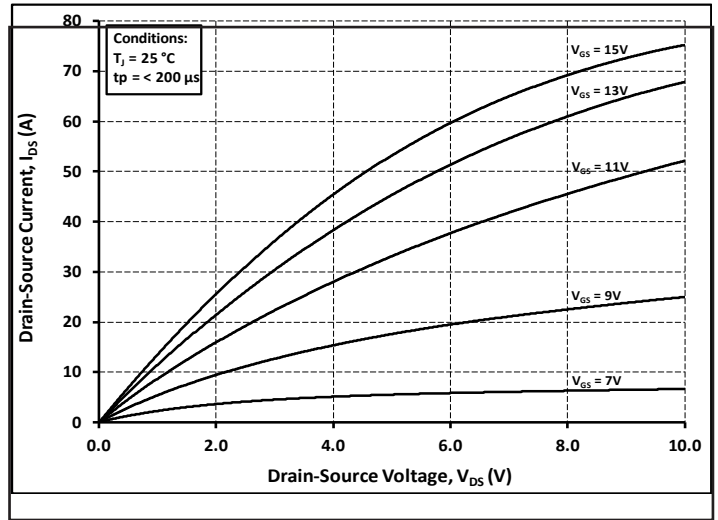


Figure 2. Output Characteristics  $T_J = 25\text{ }^\circ\text{C}$

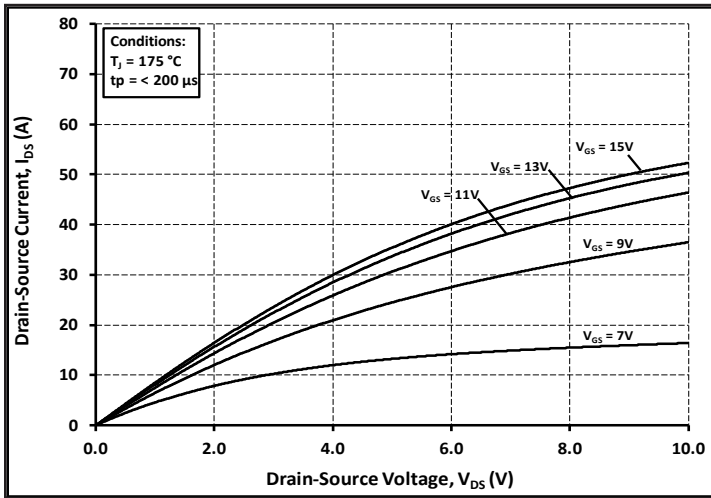


Figure 3. Output Characteristics  $T_J = 175\text{ }^\circ\text{C}$

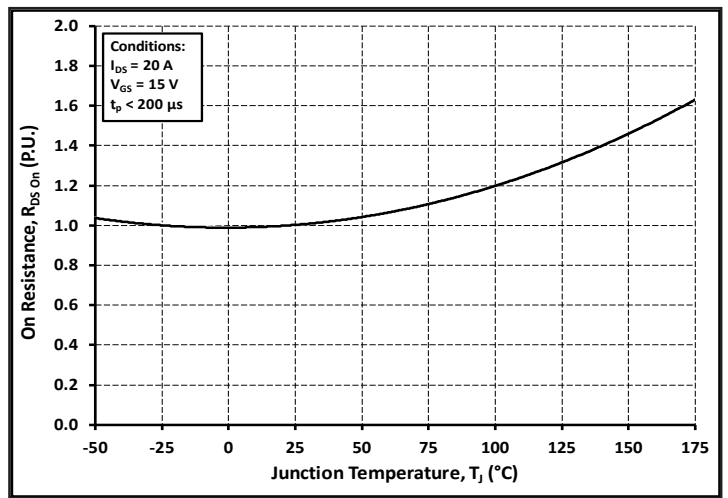


Figure 4. Normalized On-Resistance vs. Temperature

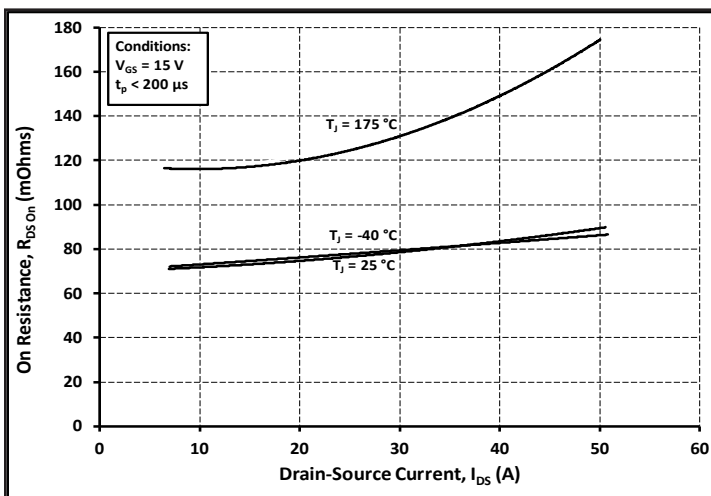


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

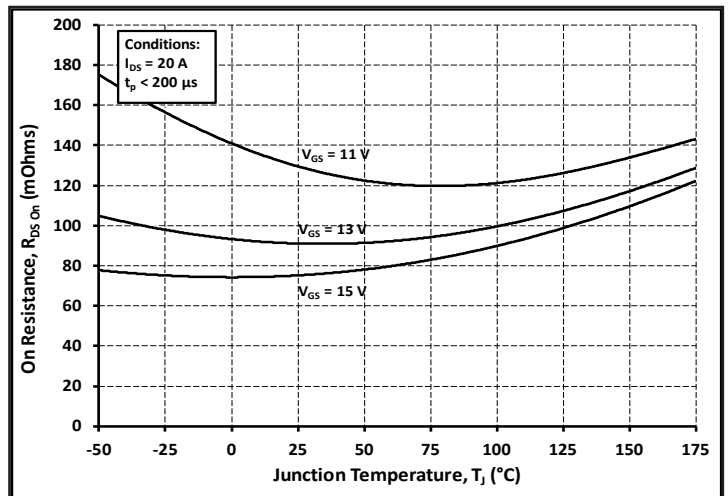


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

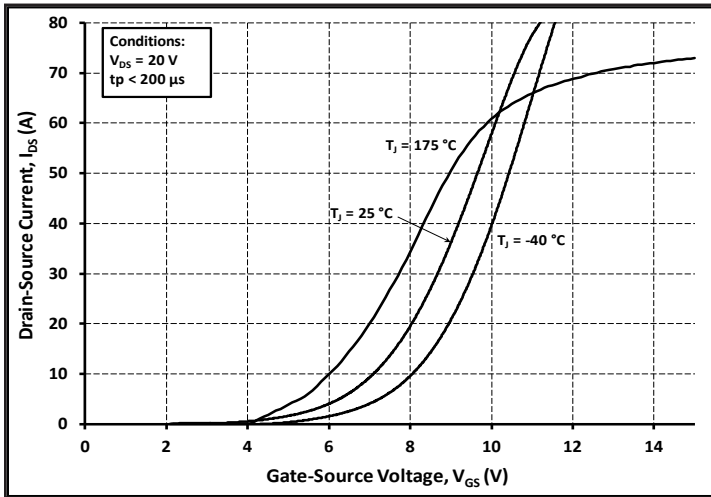


Figure 7. Transfer Characteristic for Various Junction Temperatures

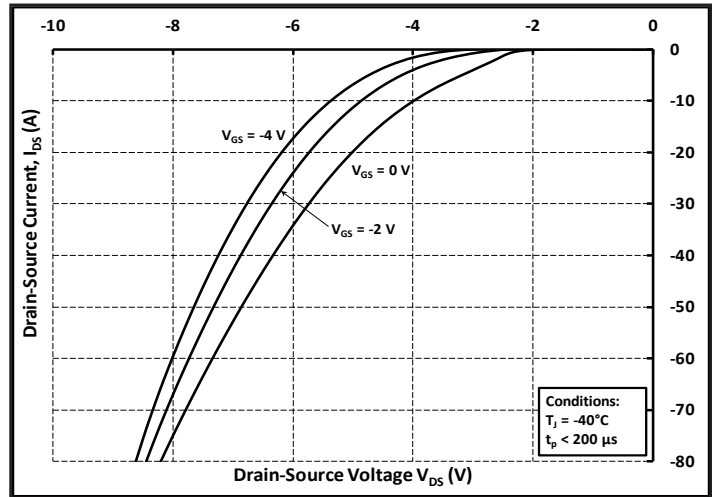


Figure 8. Body Diode Characteristic at -40 °C

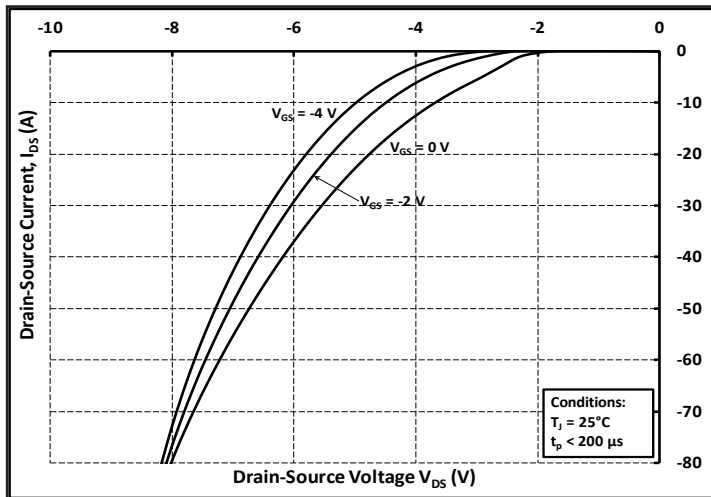


Figure 9. Body Diode Characteristic at 25 °C

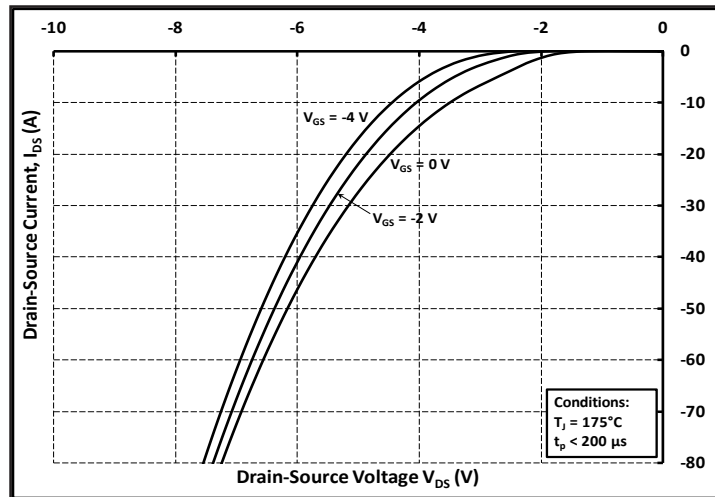


Figure 10. Body Diode Characteristic at 175 °C

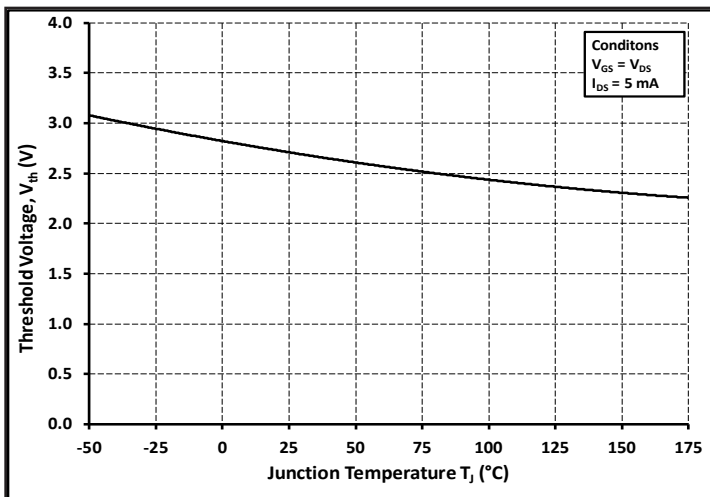


Figure 11. Threshold Voltage vs. Temperature

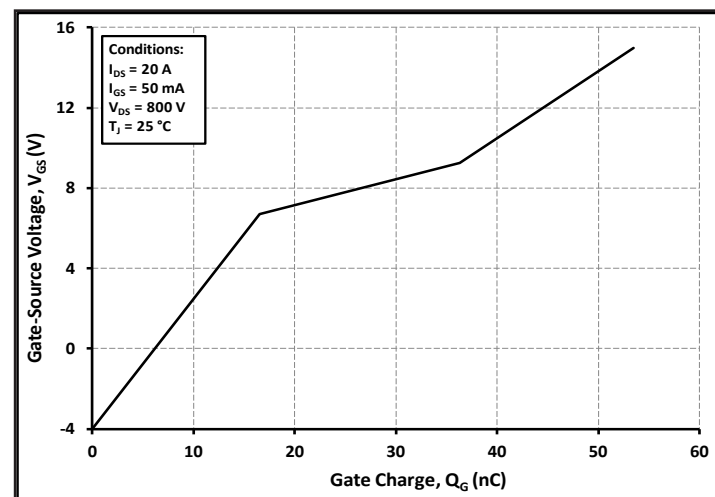


Figure 12. Gate Charge Characteristics

Typical Performance

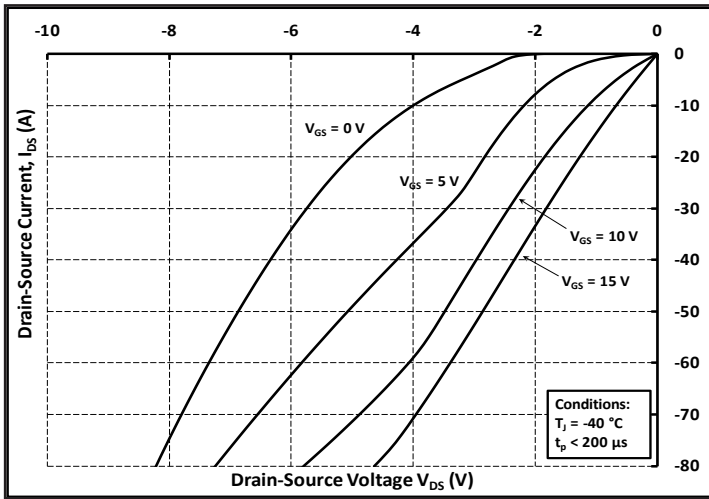


Figure 13. 3rd Quadrant Characteristic at  $-40\text{ }^\circ\text{C}$

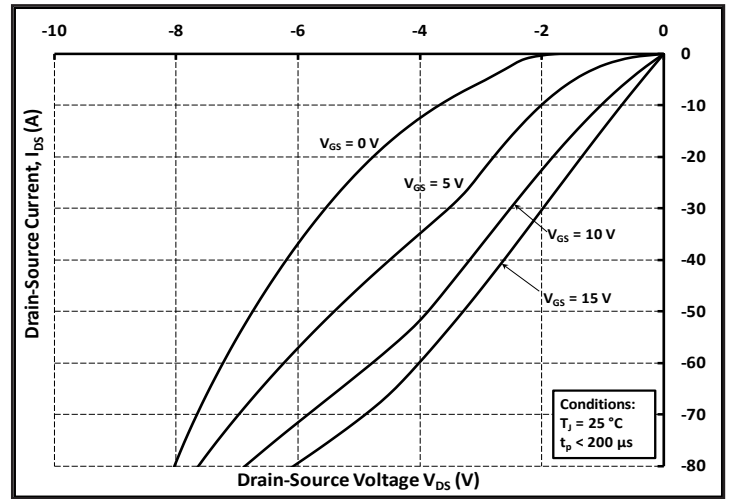


Figure 14. 3rd Quadrant Characteristic at  $25\text{ }^\circ\text{C}$

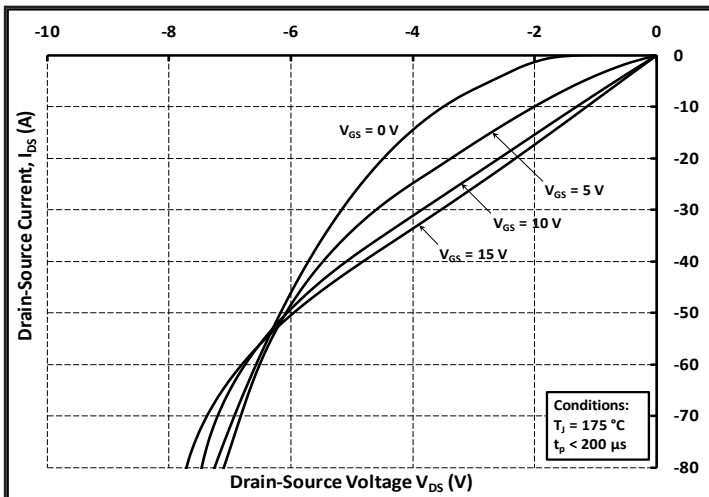


Figure 15. 3rd Quadrant Characteristic at  $175\text{ }^\circ\text{C}$

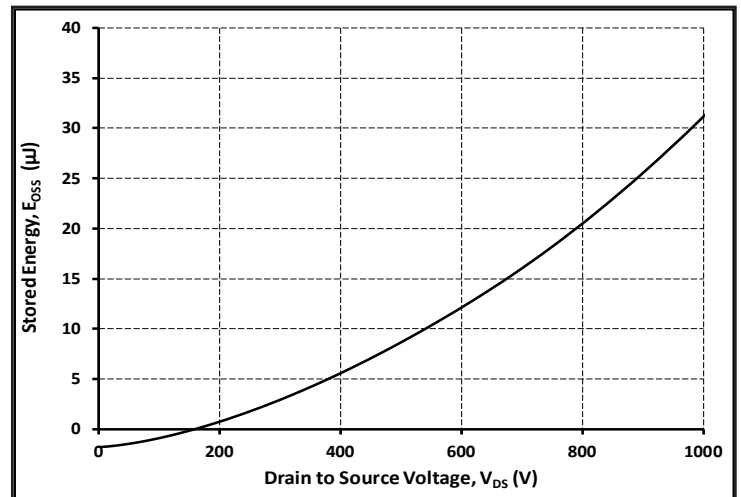


Figure 16. Output Capacitor Stored Energy

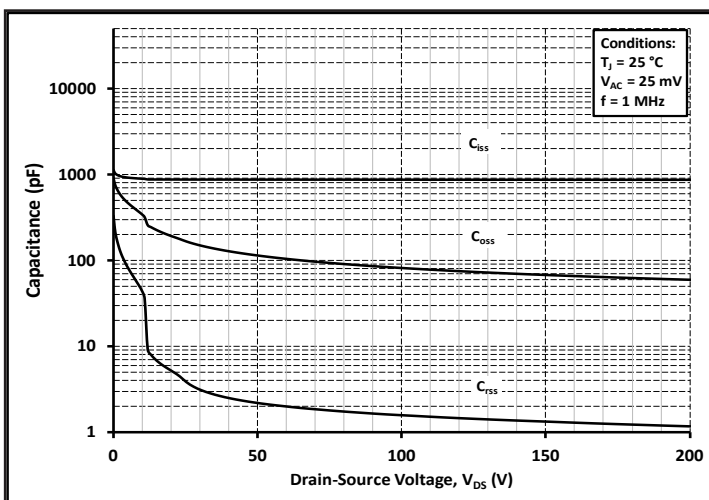


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

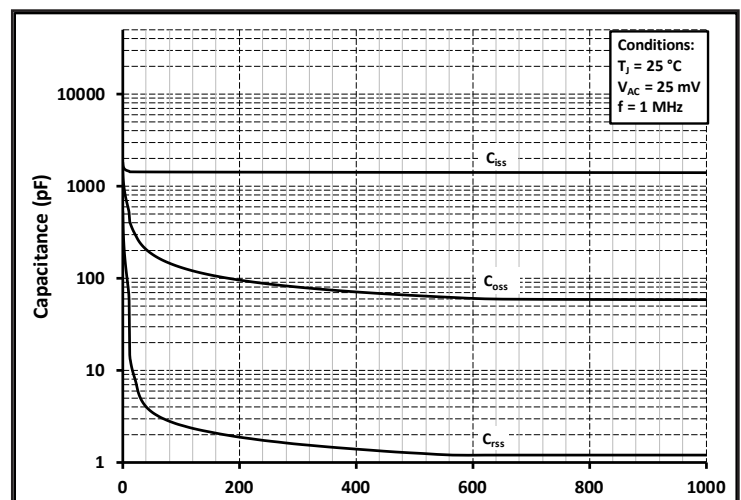


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)

Typical Performance

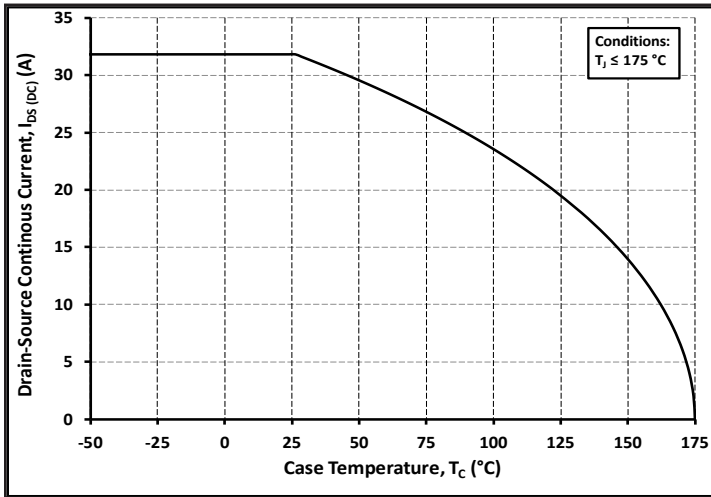


Figure 19. Continuous Drain Current Derating vs. Case Temperature

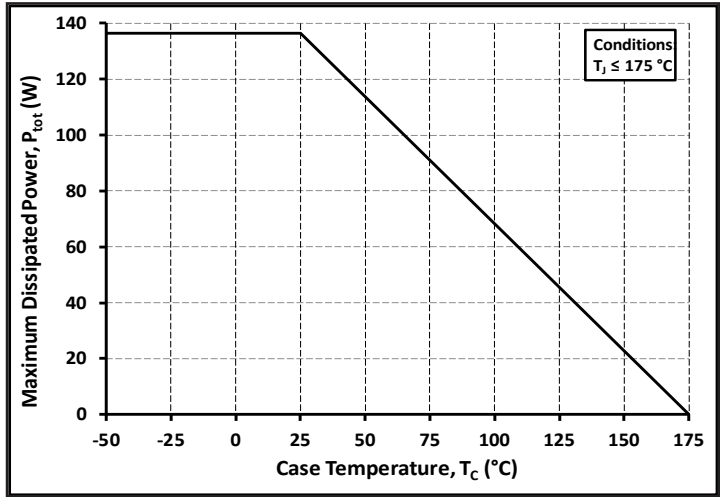


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

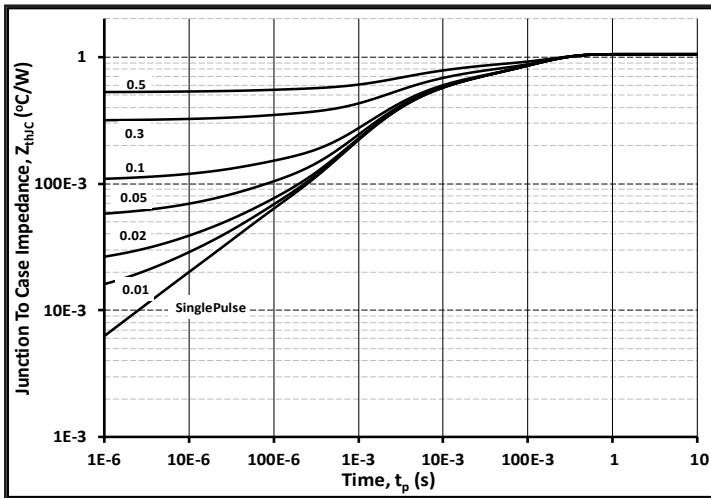


Figure 21. Transient Thermal Impedance (Junction - Case)

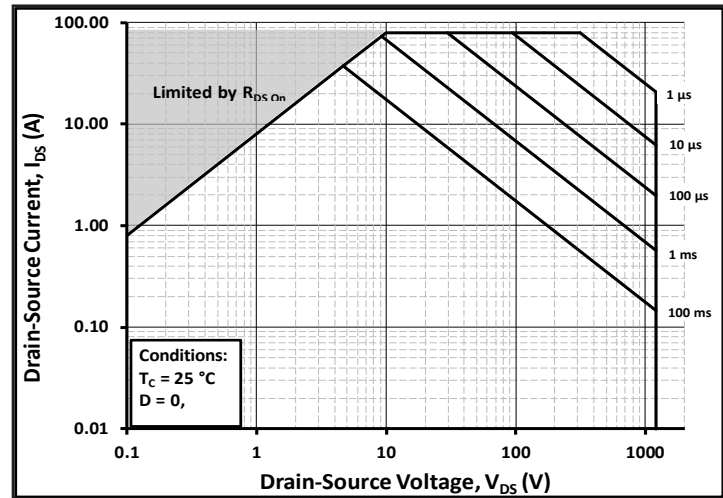


Figure 22. Safe Operating Area

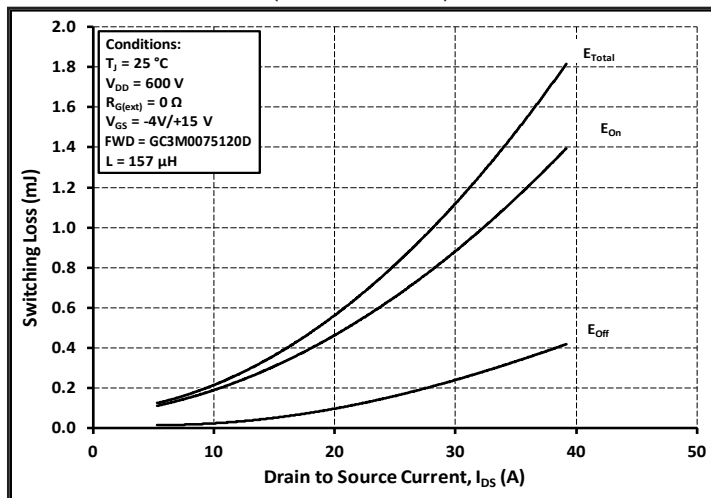


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 600V$ )

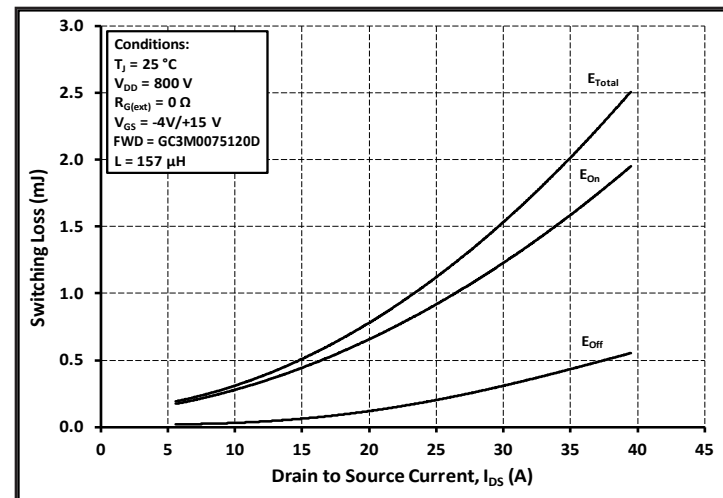


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 800V$ )

Typical Performance

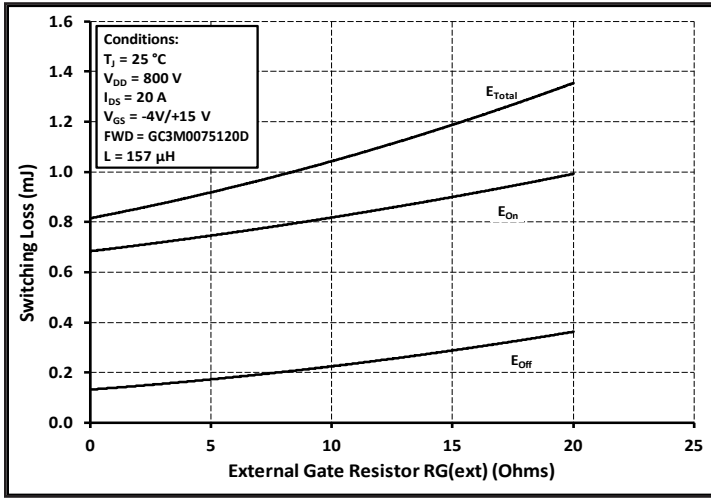


Figure 25. Clamped Inductive Switching Energy vs.  $R_{G(ext)}$

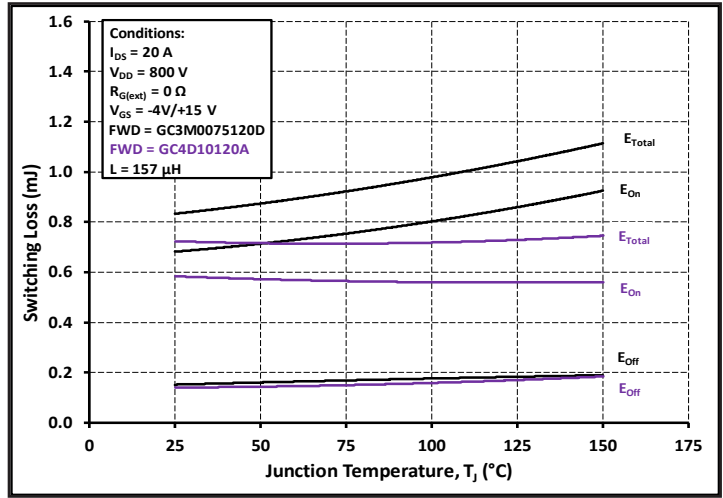


Figure 26. Clamped Inductive Switching Energy vs. Temperature

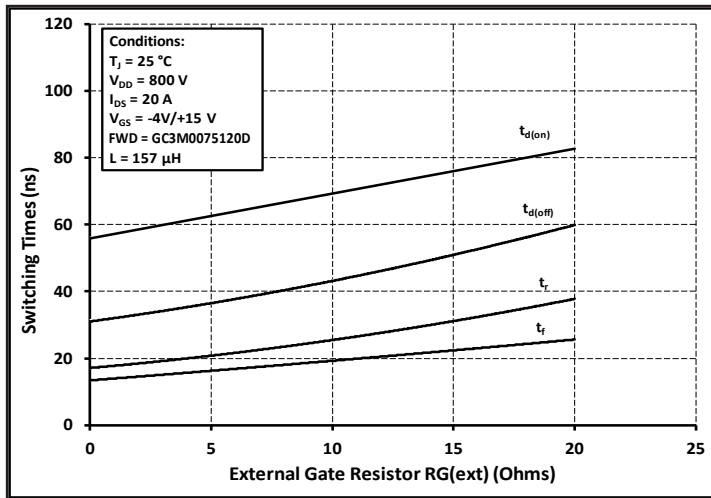


Figure 27. Switching Times vs.  $R_{G(ext)}$

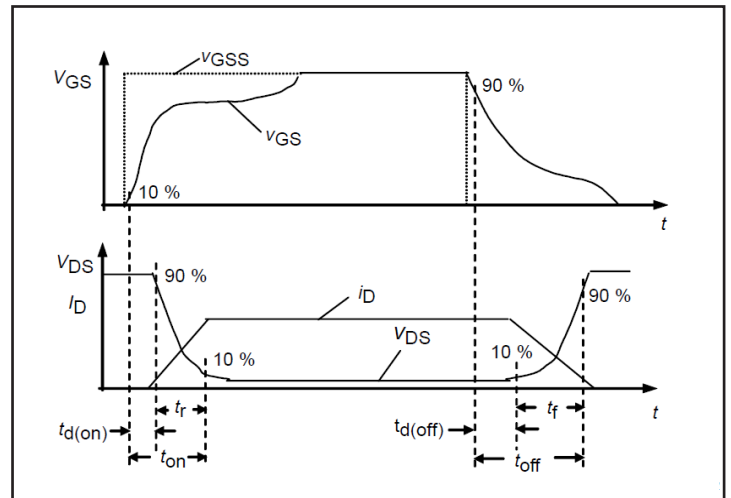


Figure 28. Switching Times Definition

**Test Circuit Schematic**

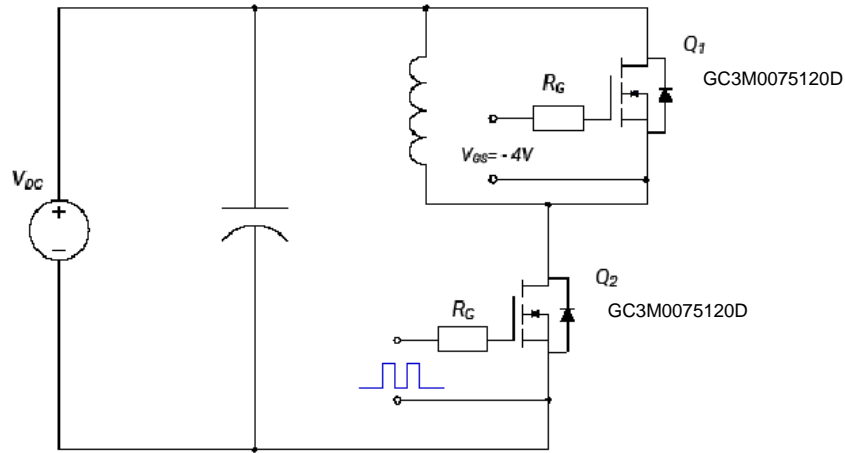


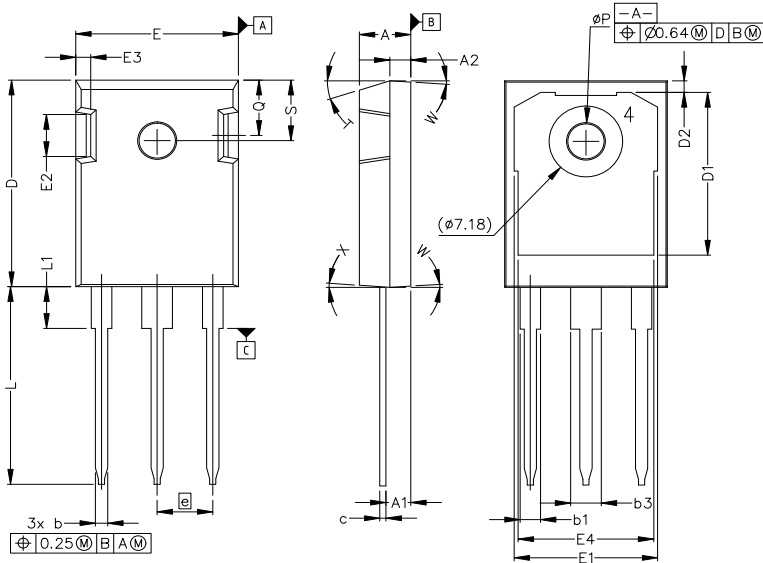
Figure 29. Clamped Inductive Switching  
Waveform Test Circuit

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode as shown above.



## Package Dimensions

Package TO-247-3

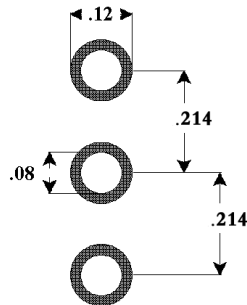


Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

SYM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.07	1.33	.042	.052
b1	1.91	2.41	.075	.095
b3	2.87	3.38	.113	.133
c	0.55	0.68	.022	.027
D	20.80	21.10	.819	.831
D1	16.25	17.65	.640	.695
D2	0.95	1.25	.037	.049
E	15.75	16.13	.620	.635
E1	13.10	14.15	.516	.557
E2	3.68	5.10	.145	.201
E3	1.00	1.90	.039	.075
E4	12.38	13.43	.487	.529
e	5.44 BSC		.214 BSC	
N	3		3	
L	19.81	20.32	.780	.800
L1	4.10	4.40	.161	.173
$\phi P$	3.51	3.65	.138	.144
Q	5.49	6.00	.216	.236
S	6.04	6.30	.238	.248
T	17.5° REF.			
W	3.5° REF.			
X	4° REF.			

## Recommended Solder Pad Layout



TO-247-3

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [SiC MOSFETs](#) category:*

*Click to view products by [SUPSiC](#) manufacturer:*

Other Similar products are found below :

[NTC040N120SC1](#) [HC3M001K170J](#) [IMBG65R048M1HXTMA1](#) [IMW120R045M1](#) [SCTWA70N120G2V-4](#) [SCT040HU65G3AG](#)  
[SCTWA90N65G2V](#) [GC3M0060065K](#) [GC3M0120090D](#) [GC3M0032120D](#) [GC3M0160120D](#) [GC3M0040120K](#) [GC3M0021120D](#)  
[GC3M0065090D](#) [GC3M0032120K](#) [GC3M0065100K](#) [GC3M0075120K](#) [GC2M0040120D](#) [GC3M0280090D](#) [GC2M0025120D](#)  
[GC3M0075120D](#) [GC3M0040120D](#) [GC2M0280120D](#) [GC2M0080120K](#) [GC3M0016120D](#) [GC2M0045170D](#) [GC2M0160120K](#)  
[GC3M0021120K](#) [SP25N120CTK](#) [SP90N120CTK](#) [GC3M0080120K](#) [SP50N120CTK](#) [GC2M0160120D](#) [GC2M1000170D](#) [GC3M0120100K](#)  
[GC2M0080120D](#) [SP50N120CTF](#) [SP35N120CTF](#) [SP25N120CTF](#) [IV2Q171R0D7](#) [IV1Q06040L1](#) [IV1Q06060T3G](#) [IV1Q12160T4](#)  
[IV1B12013HA1L](#) [IV1Q12160T3](#) [IV1Q07015T4G](#) [IV1Q12750O3](#) [IV1Q06040T3](#) [IV1Q12050T4Z](#) [IV1Q12030T4G](#)